#### 503091245 12/08/2014

### PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT3137850

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

#### **CONVEYING PARTY DATA**

Name	Execution Date
Kuan-Yu Chen	10/24/2014
Tseng-Hsun Liu	10/27/2014
Min-Hsuan Tsai	12/03/2014
Te-Chang Chiu	12/03/2014
Chiu-Ling Lee	12/03/2014
Chiu-Te Lee	12/03/2014

#### **RECEIVING PARTY DATA**

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Street Address:	No.3, Li-Hsin Road 2, Science-Based Industrial Park
City:	Hsin-Chu City
State/Country:	TAIWAN

#### **PROPERTY NUMBERS Total: 1**

Property Type	Number
Application Number:	14564050

#### **CORRESPONDENCE DATA**

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**Correspondent Name:** WINSTON HSU **Address Line 1:** P.O.BOX 506

Address Line 4: MERRIFIELD, VIRGINIA 22116

ATTORNEY DOCKET NUMBER:	NAUP2370USA
NAME OF SUBMITTER:	KATE YEH
SIGNATURE:	/KATE YEH/
DATE SIGNED:	12/08/2014

**Total Attachments: 12** source=2124807#page1.tif source=2124807#page2.tif

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#### Title of Invention:

### HIGH VOLTAGE SEMICONDUCTOR DEVICES WITH SCHOTTKY DIODES

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	filed on	, or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made	by me.	
I believe that I am the original invente application.	or or an original joint inventor of a	a claimed invention in th	e
I hereby acknowledge that any willful under18 U.S.C. 1001 by fine or impri			
In consideration of the payment by	UNITED MICROELECTRON	NICS having a posta	al address of
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, Hs	in-Chu City 300, Tai	wan, R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	o I of the sum of One Dollar (\$ 1.0 d valuable consideration.	00), the receipt of which	is hereby
I hereby sell, assign and transfer to A the entire right, title and interest in ar invention as above-identified application or invention by the above application or substitutes, or extensions thereof, an	nd to any and all improvements w tion and, in and to, all Letters Pat any continuations, continuation-	hich are disclosed in the ent to be obtained for sa in-part, divisions, renew	e aid als,
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representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	lication, said invention and said L cessary or desirable to carry out	etters Patent and said the proposes thereof.	ate of signing)
Note: An application data sheet (PTC inventive entity, must accompany this			

Page 1 of 12

LEGAL NAME OF INVENTOR(ASSIGNOR)

Inventor:

Kuan-Yu Chen

Date:

2014/10/24

Signature:

B東辽宁 Vivan Xu Chen

Page 2 of 12

F#NPO-P0002E-US1201 DSC0-103U009468

CUST#UMCD-2014-0433

NPO#NAU-P2370-USA:0

#### Title of Invention:

## HIGH VOLTAGE SEMICONDUCTOR DEVICES WITH SCHOTTKY DIODES

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☑ The attached application, or	r		
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☐ PCT international applicatio	n number	filed on	_
The above-identified application wa	s made or authorized to be mad	e by me.	
I believe that I am the original inven application.	tor or an original joint inventor of	f a claimed invention in the	
I hereby acknowledge that any willfuunder18 U.S.C. 1001 by fine or imp	ul false statement made in this d risonment of not more than five	eclaration is punishable (5) years, or both.	
In consideration of the payment by	UNITED MICROELECTRO	ONICS having a postal add	dress of
No.3, Li-Hsin Road 2, Science	e-Based Industrial Park, H	sin-Chu City 300, Taiwar	ı, R.O.C.
(referred to as "ASSIGNEE"below) t acknowledged, andfor other good a	to I of the sum of One Dollar (\$ 1 nd valuable consideration.	.00), the receipt of which is he	ereby
I hereby sell, assign and transfer to the entire right, title and interest in a invention as above-identified applica- invention by the above application o substitutes, or extensions thereof, a	and to any and all improvements ation and, in and to, all Letters P or any continuations, continuation	which are disclosed in the atent to be obtained for said n-in-part, divisions, renewals.	NEE
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I further covenant that ASSIGNEE wand documents relating to said inversions and accessible to I and will to related thereto and will promptly exe	ntion and said Letters Patent and estify as to the same in any inter	d legal equivalents as may be ference, litigation proceeding	cts
representatives any and all papers, maintain, issue and enforce said ap equivalents thereof which may be no IN WINTNESS WHEREOF, I have h	plication, said invention and said ecessary or desirable to carry ou	Letters Patent and said	of signing)
Note: An application data sheet (PT inventive entity, must accompany the	O/SB/14 or equivalent), including is form. Use this form for each a	g naming the entire dditional inventor.	

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Page 4 of 12

NPO#NAU-P2370-USA:0 CUST#UMCD-2014-0433

#### Title of Invention:

#### HIGH VOLTAGE SEMICONDUCTOR DEVICES WITH SCHOTTKY DIODES

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(referred to as "ASSIGNEE"below) to acknowledged, andfor other good ar		0), the receipt of which	ch is hereby
I hereby sell, assign and transfer to a the entire right, title and interest in a invention as above-identified applica invention by the above application of substitutes, or extensions thereof, ar	nd to any and all improvements w tion and, in and to, all Letters Pat r any continuations, continuation-i	hich are disclosed in ent to be obtained for n-part, divisions, rene	the r said ewals,
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encumbran n this assignment;	ce has been or will b	e made or
I further covenant that ASSIGNEE wand documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ntion and said Letters Patent and stify as to the same in any interfe	legal equivalents as r rence, litigation proce	nay be
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be no IN WINTNESS WHEREOF, I have h	olication, said invention and said L ecessary or desirable to carry out	etters Patent and sai	id (Date of signing)
Note: An application data sheet (PT0 inventive entity, must accompany thi			

Page 5 of 12

NPO#NAU-P2370-USA:0 CUST#UMCD-2014-0433

LEGAL NAME OF INVENTOR(ASSIGNOR)

Inventor:

Min-Hsuan Tsai

Date:

DEC 0 3 2014

Signature: Min }

Page 6 of 12

F#NPO-P0002E-US1201 DSC0-103U010682

NPO#NAU-P2370-USA:0 CUST#UMCD-2014-0433

#### Title of Invention:

## HIGH VOLTAGE SEMICONDUCTOR DEVICES WITH SCHOTTKY DIODES

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☑ The attached application, or				
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☐ PCT international application	number	file	d on	
The above-identified application was	made or authorized to	be made by me.		
I believe that I am the original inventagplication.	or or an original joint inv	entor of a claime	d invention in the	
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impri	I false statement made isonment of not more th	in this declaration an five (5) years,	is punishable or both.	
In consideration of the payment by	UNITED MICROEL CORP.	ECTRONICS	having a postal add	ress of
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I hereby sell, assign and transfer to A the entire right, title and interest in ar invention as above-identified applica- invention by the above application or substitutes, or extensions thereof, an	nd to any and all improvition and, in and to, all L any continuations, con	ements which are etters Patent to b tinuation-in-part.	e disclosed in the e obtained for said divisions, renewals.	EE
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or en n this assignment;	ncumbrance has	been or will be made	or
I further covenant that ASSIGNEE wi and documents relating to said inven known and accessible to I and will te related thereto and will promptly exec	tion and said Letters Pa stify as to the same in a	atent and legal equiny interference, I	uivalents as may be itigation proceeding	ts
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	lication, said invention a cessary or desirable to	and said Letters F carry out the prop	Patent and said poses thereof.	f signing)
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), is form. Use this form for	including naming each additional i	the entire nventor.	

Page 7 of 12

LEGAL NAM	ME OF INVENTOR(ASSIGNOR)		•	
Inventor:	Te-Chang Chiu	Date:	DEC 0 3 2014	
Signature:	Te Chang Chin			

Page 8 of 12

NPO#NAU-P2370-USA:0 CUST#UMCD-2014-0433

#### Title of Invention:

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representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	lication, said invention and said L cessary or desirable to carry out i	etters Patent and	said
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), including is form. Use this form for <u>each add</u>	naming the entire ditional inventor.	

Page 9 of 12

LEGAL NAME OF INVENTOR(ASSIGNOR)							
Inventor:	Chiu-Ling Lee	Date:	DEC 0 3 2014				
Signature:	Chir-Ling Lee						

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NPO#NAU-P2370-USA:0 CUST#UMCD-2014-0433

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representatives any and all papers, ir maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have he	lication, said inventio	n and said Letter to carry out the p	s Patent and sa	id : (Date of signing) 
Note: An application data sheet (PTC inventive entity, must accompany this				

Page 11 of 12

NPO#NAU-P2370-USA:0 CUST#UMCD-2014-0433

Inventor: Chiu-Te Lee Date: DEC 0 3 2014

Signature: Mur-Te Les

Page 12 of 12

NPO#NAU-P2370-USA:0 CUST#UMCD-2014-0433

**RECORDED: 12/08/2014** 

F#NPO-P0002E-US1201 DSC0-103U009468